

**LISTING OF CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in the  
Application:

**Claims 1-13 (canceled)**

**Claim 14 (new):** A method for forming a multi-level interconnection structure in a  
semiconductor device, said method comprising the steps of:

forming first level interconnections overlying a substrate;

consecutively forming first and second dielectric films on said first level  
interconnections;

consecutively forming first through third hard mask films on said second dielectric film,  
said first through third hard mask films being insulating films;

selectively etching said second and third hard mask films to form a through-hole pattern  
on said second and third hard mask films;

selectively etching said third hard mask film to form a trench pattern on said third hard  
mask film, said trench pattern partially overlapping said through-hole pattern;

selectively etching said first hard mask film by using said second hard mask film as an  
etching mask to form said through-hole pattern on said first hard mask film;

selectively etching said second dielectric film by using said first hard mask film as an  
etching mask to form first through-holes in said second dielectric film based on said through-  
hole pattern;

selectively etching said first and second hard mask films and a top portion of said first  
dielectric film by using said third hard mask film as an etching mask to form trenches in said first

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and second hard mask films and said top portion of said second dielectric film based on said trench pattern; and

selectively etching said first dielectric film to form therein second through-holes communicated with respective said first through-holes for exposing part of said first level interconnections through said first and second through-holes.

**Claim 15 (new):** The method as defined in claim 14, wherein at least said three hard mask films are in direct contact with each other and are made of different materials.

**Claim 16 (new):** The method as defined in claim 14, wherein at least said three hard mask films are in direct contact with each other and have different etching rates.

**Claim 17 (new):** The method as defined in claim 14 wherein, in said second and third hard mask films etching step, a first anti-reflection film is formed on said third hard mask, a first etching film having a through-hole pattern is formed on said first anti-reflection film, and said first anti-reflection film and subsequently said third and second hard mask films are etched.

**Claim 18 (new):** The method as defined in claim 14, wherein, in said third hard mask film etching step, a second anti-reflection film is formed on said third hard mask for filling the first through-hole pattern, a second etching mask having a trench pattern is formed on the second anti-reflection film, and said second anti-reflection film and subsequently said third hard mask film are etched.

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